

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
-20V	15mΩ @ V _{GS} = -4.5V	-9.5A
	19mΩ @ V _{GS} = -2.5V	-8.5A

Features and Benefits

- 0.6mm Profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Low On-Resistance
- ESD-Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

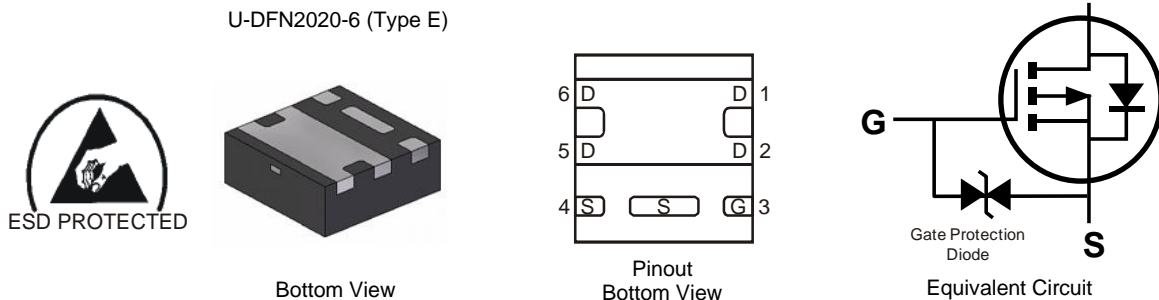
Description and Applications

This MOSFET is designed to minimize on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Battery-management applications
- Power-management functions
- DC-DC converters

Mechanical Data

- Package: U-DFN2020-6
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 Ⓔ4
- Weight: 0.007 grams (Approximate)



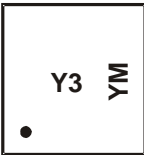
Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMP2016UFDE-7	U-DFN2020-6 (Type E)	3,000	Tape & Reel
DMP2016UFDE-13	U-DFN2020-6 (Type E)	10,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

Site 1

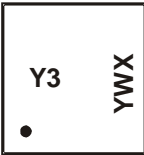


Y3 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: L = 2024)
 M = Month (ex: 9 = September)

Date Code Key

Year	2020	-	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	H	-	L	M	N	P	R	S	T	U	V	W
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Site 2



Y3 = Product Type Marking Code
 YWX = Date Code Marking
 Y = Year (ex: 4 = 2024)
 W = Week (ex: a = week 27; z represents week 52 and 53)
 X = Internal code (ex: U = Monday)

Date Code Key

Year	2020	-	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	0	-	4	5	6	7	8	9	0	1	2	3
Week	1-26				27-52				53			
Code	A-Z				a-z				z			
Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat					
Code	T	U	V	W	X	Y	Z					

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V_{GSS}	± 8	V
Continuous Drain Current (Note 5) $V_{GS} = -4.5\text{V}$	Steady State	I_D	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)			I_{DM}	-70
Continuous Source-Drain Diode Current (Note 5)		I_S	$T_A = +25^\circ\text{C}$	A
Avalanche Current (Note 6) $L = 0.1\text{mH}$		I_{AS}	-16.5	A
Avalanche Energy (Note 6) $L = 0.1\text{mH}$		E_{AS}	14.5	mJ

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 7)	$T_A = +25^\circ\text{C}$	P_D	0.9	W
	$T_A = +70^\circ\text{C}$		0.6	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	134	$^\circ\text{C/W}$
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$	P_D	1.8	W
	$T_A = +70^\circ\text{C}$		1.1	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	70	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case (Note 5)	Steady State	$R_{\theta JC}$	12.5	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	—	—	-1	μA	$V_{DS} = -16\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 8\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.35	—	-1.1	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	9.9	15	m Ω	$V_{GS} = -4.5\text{V}, I_D = -7.0\text{A}$
			12.5	19		$V_{GS} = -2.5\text{V}, I_D = -5.0\text{A}$
			17.5	36		$V_{GS} = -1.8\text{V}, I_D = -2.0\text{A}$
Diode Forward Voltage	V_{SD}	—	-0.6	-1.2	V	$V_{GS} = 0\text{V}, I_S = -1.0\text{A}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	1710	—	pF	$V_{DS} = -15\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	200	—		
Reverse Transfer Capacitance	C_{rss}	—	112	—		
Gate Resistance	R_g	—	28	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = -4.5\text{V}$)	Q_g	—	17	—	nC	$V_{DS} = -15\text{V}, I_D = -4.0\text{A}$
Total Gate Charge ($V_{GS} = -8\text{V}$)	Q_g	—	30	—		
Gate-Source Charge	Q_{gs}	—	2.0	—		
Gate-Drain Charge	Q_{gd}	—	3.5	—		
Turn-On Delay Time	$t_{D(ON)}$	—	6.0	—	ns	$V_{DS} = -15\text{V}, V_{GS} = -4.5\text{V}$ $R_g = 1\Omega, I_D = -4.0\text{A}$
Turn-On Rise Time	t_R	—	23	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	133	—		
Turn-Off Fall Time	t_F	—	115	—		
Reverse Recovery Time	t_{RR}	—	20	—	ns	$I_F = -1.0\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge	Q_{RR}	—	12	—	nC	$I_F = -1.0\text{A}, di/dt = 100\text{A}/\mu\text{s}$

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^\circ\text{C}$.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

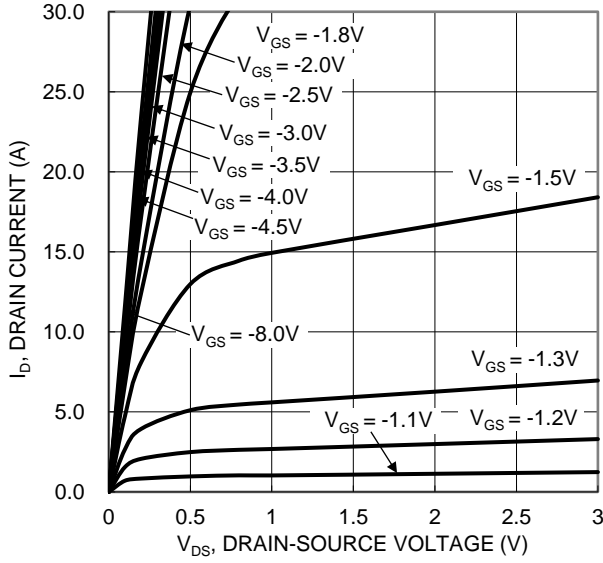


Figure 1. Typical Output Characteristic

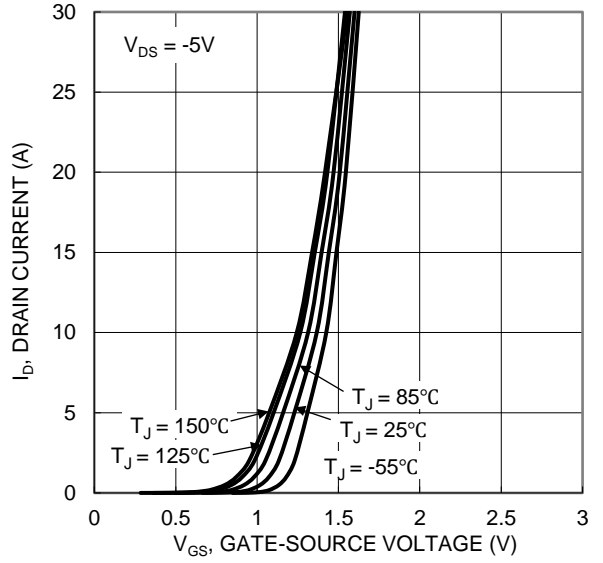


Figure 2. Typical Transfer Characteristic

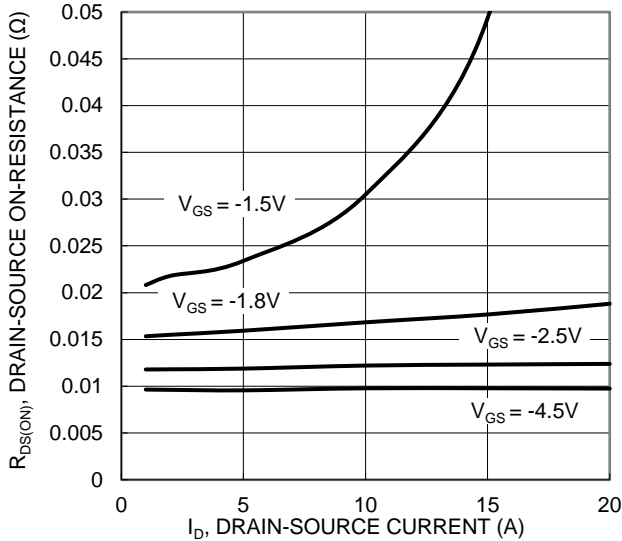


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

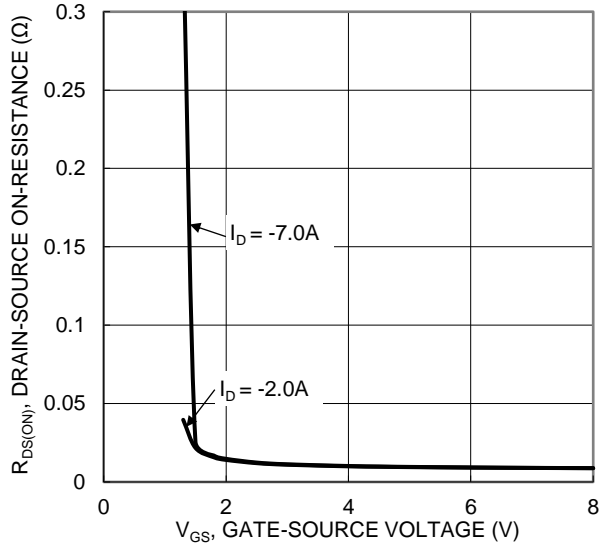


Figure 4. Typical Transfer Characteristic

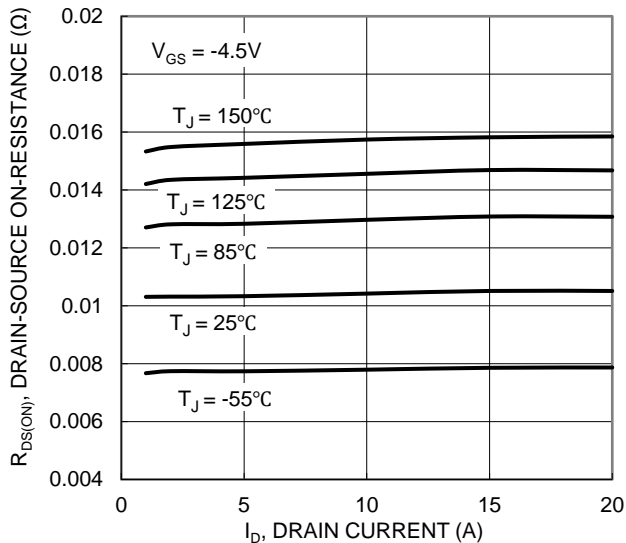


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

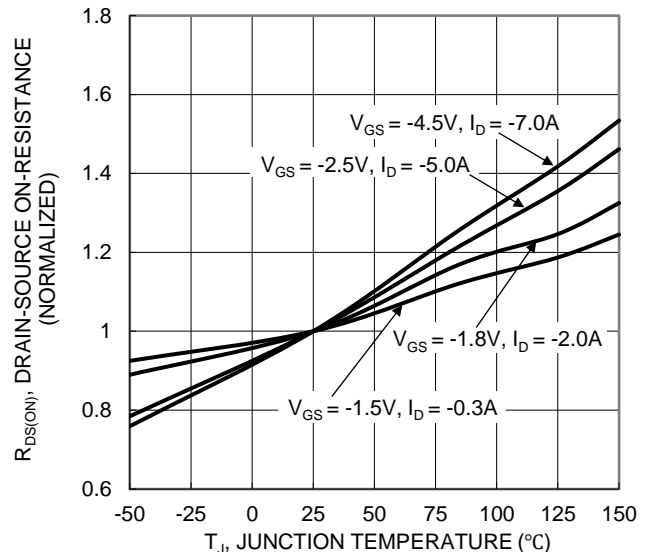


Figure 6. On-Resistance Variation with Junction Temperature

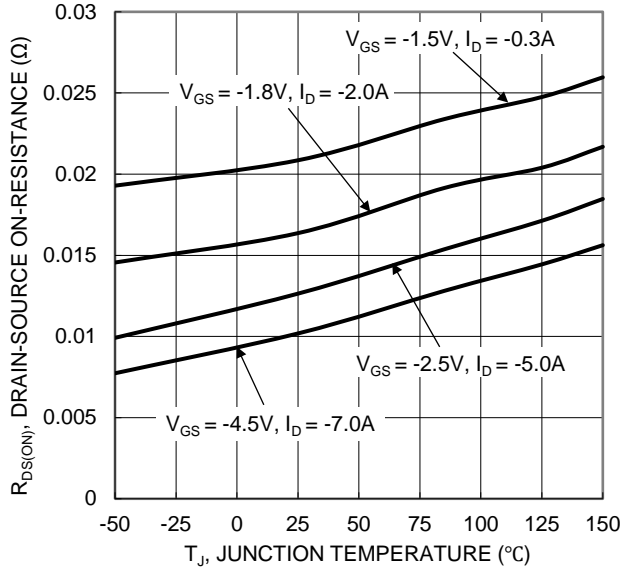


Figure 7. On-Resistance Variation with Junction Temperature

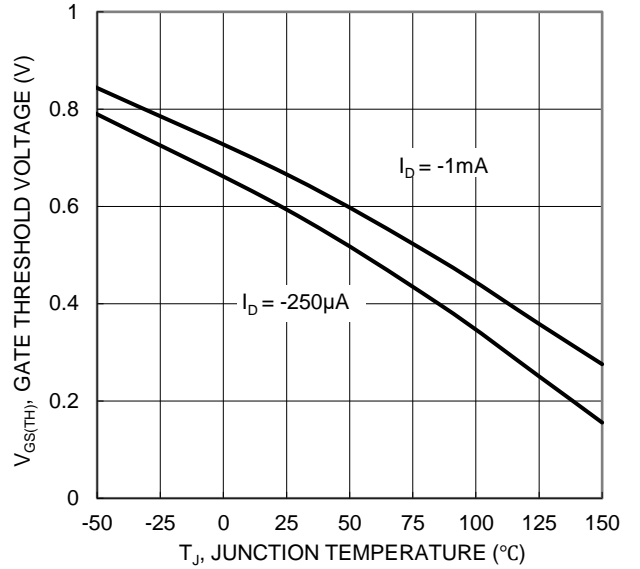


Figure 8. Gate Threshold Variation vs. Junction Temperature

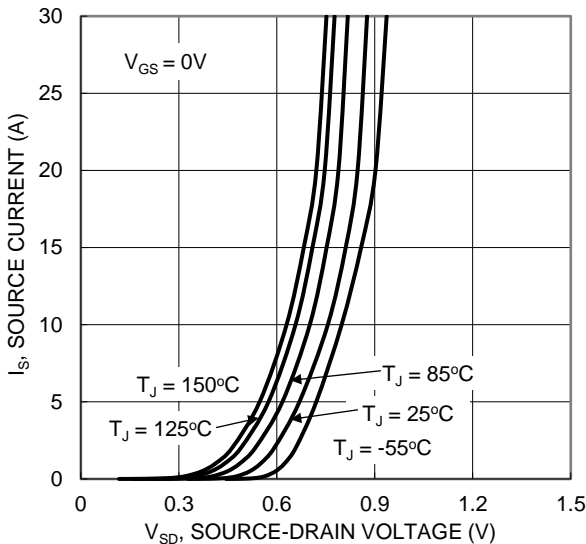


Figure 9. Diode Forward Voltage vs. Current

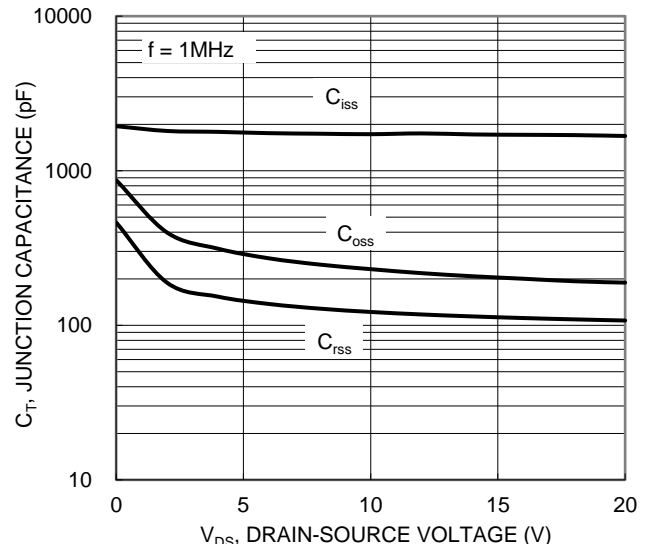


Figure 10. Typical Junction Capacitance

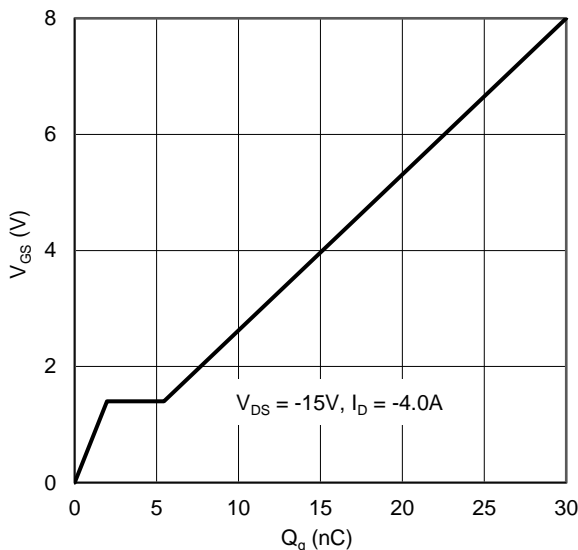


Figure 11. Gate Charge

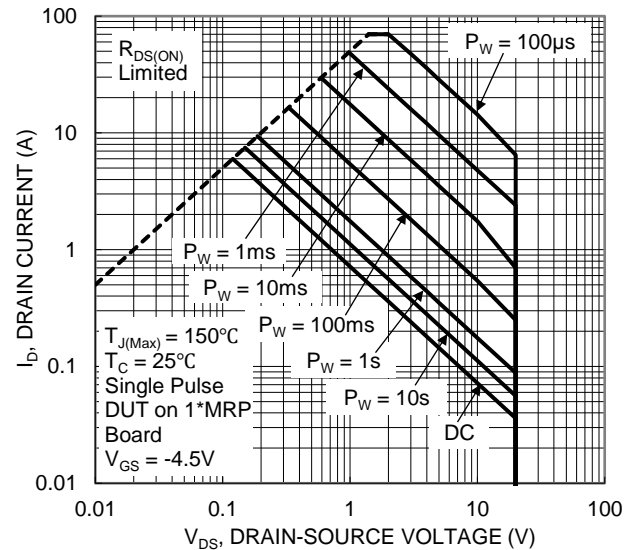


Figure 12. SOA, Safe Operation Area

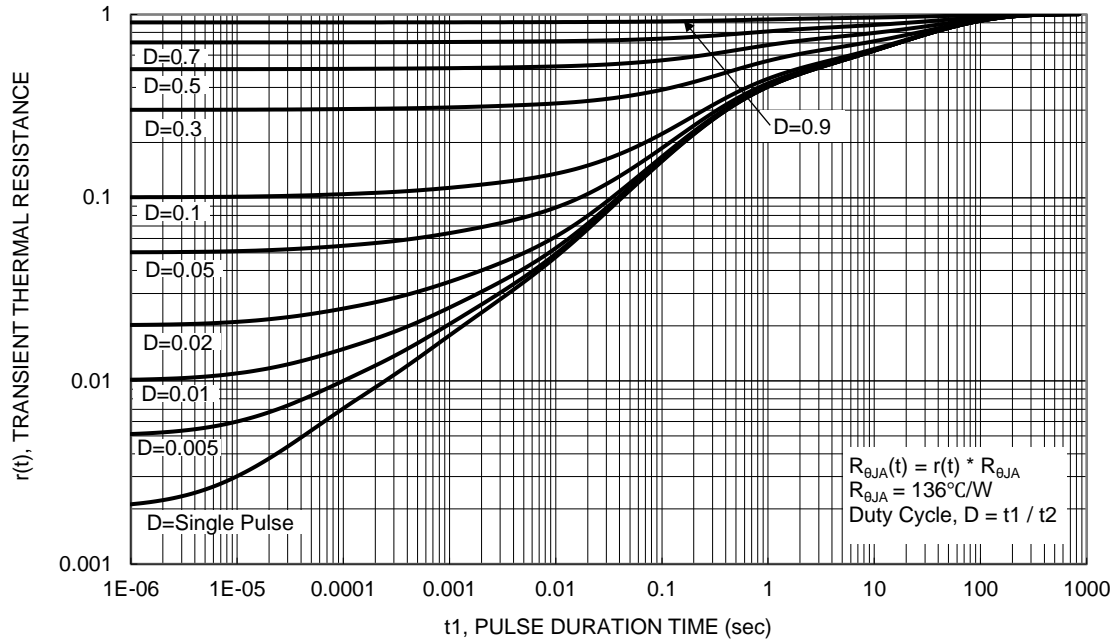
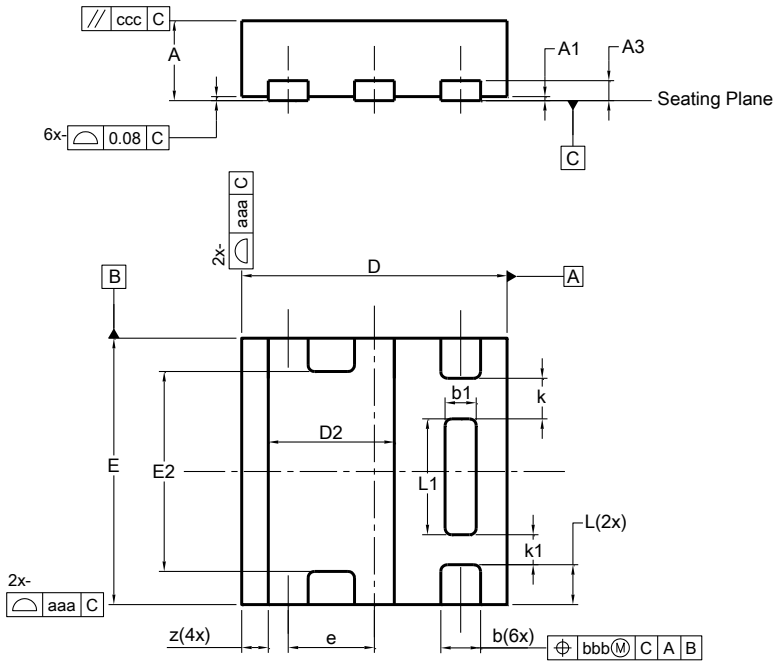


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type E)

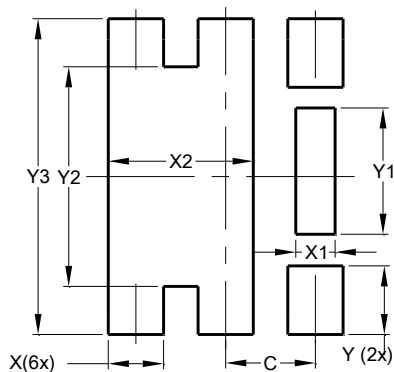


U-DFN2020-6 (Type E)			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	-	-	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
k	-	-	0.305
k1	-	-	0.225
Z	-	-	0.20
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type E)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

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